

Application No. 09/910,447
Amtd. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate having an indented section;
a gate dielectric layer formed disposed on the indented section;
a gate electrode formed disposed on the gate dielectric layer, wherein a portion of the gate electrode is embedded in the semiconductor substrate and another portion of the gate electrode is above the semiconductor substrate;
first and second impurity diffusion layers formed disposed in the semiconductor substrate and opposed to each other with the gate electrode being interposed between them;
a third impurity diffusion layer formed disposed in a portion immediately below the gate electrode in the semiconductor substrate; and
a sidewall dielectric layer formed disposed on a side surface section of the gate electrode, wherein the gate electrode has a width that gradually increases from a bottom thereof up to toward an upper surface thereof, and
wherein surfaces of the first and second impurity diffusion layers are located at a position higher than an interface between the semiconductor substrate and the gate dielectric layer.

2. (Original) A semiconductor device according to claim 1, wherein a distance between the surface of the first and second impurity diffusion layers and the interface between the semiconductor substrate and the gate dielectric layer is between about 0.05 and 0.15 μ m.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

3. (Currently amended) A semiconductor device according to claim 1, wherein a groove section is formed disposed at a specified location in the semiconductor substrate, and the gate electrode is formed disposed on a bottom surface of the groove section through the gate dielectric layer.

4. (Currently amended) A semiconductor device according to claim 1, wherein the gate electrode is formed disposed from at least one alloy that includes at least two constituents selected from the following group:

polycrystalline silicon, tungsten, tantalum, copper and gold.

5. - 6. (Cancelled)

7. (Previously Presented) A semiconductor device according to claim 1, wherein the first and second impurity diffusion layers include an extension region.

8. (Cancelled)

9. (Currently Amended) A semiconductor device according to claim 1, wherein a first metal silicide layer is formed disposed on the first and second impurity diffusion layers, and the gate electrode includes a second metal silicide layer on an upper surface thereof.

10. (Cancelled)

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

11. (Currently Amended) A semiconductor device according to claim 1, wherein surfaces of the first and second impurity diffusion layers are formed disposed at a position higher than a surface of the an element isolation region.

12 – 20 (Cancelled)

21. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate having an indented section;
a gate dielectric layer formed disposed on the indented section;
a gate electrode formed disposed on the gate dielectric layer, wherein a portion of the gate electrode is embedded in the semiconductor substrate and another portion of the gate electrode is above the semiconductor substrate;
first and second impurity diffusion layers formed disposed in the semiconductor substrate and opposed to each other with the gate electrode being interposed between them; and
a sidewall dielectric layer formed disposed on a side surface section of the gate electrode, wherein the gate electrode has a width that gradually increases from a bottom thereof up to toward an upper surface thereof,
wherein surfaces of the first and second impurity diffusion layers are located at a position higher than an interface between the semiconductor substrate and the gate dielectric layer, and
wherein surfaces of the first and second impurity diffusion layers are formed disposed at a position higher than a surface of the an element isolation region.

22. (Previously Presented) A semiconductor device according to claim 21, wherein a distance between the surface of the first and second impurity diffusion layers and the interface between the semiconductor substrate and the gate dielectric layer is between about 0.05 and 0.15 μ m.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

23. (Currently amended) A semiconductor device according to claim 21, wherein a groove section is formed disposed at a specified location in the semiconductor substrate, and the gate electrode is formed disposed on a bottom surface of the groove section through the gate dielectric layer.

24. (Currently amended) A semiconductor device according to claim 21, wherein the gate electrode is formed disposed from at least one alloy that includes at least two constituents selected from the following group:

polycrystalline silicon, tungsten, tantalum, copper and gold.

25.-27. (Cancelled)

28. (Previously Presented) A semiconductor device according to claim 21, further comprising:

a third impurity diffusion layer immediately below the gate electrode in the semiconductor substrate, wherein the third impurity diffusion layer is of the opposite conductivity type as the semiconductor substrate, and wherein the first and second impurity diffusion layers include an extension region.

29. (Currently amended) A semiconductor device according to claim 21, wherein a first metal silicide layer is formed disposed on the first and second impurity diffusion layers, and the gate electrode includes a second metal silicide layer on an upper surface thereof.

30. (Cancelled)

Application No. 09/910,447
Amtd. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

31. (Currently amended) A semiconductor device according to claim 21, wherein the sidewall dielectric layer has an outer surface that is generally vertical with respect to the surface of the semiconductor substrate, and a film thickness that gradually reduces from a bottom thereof up to toward an upper surface thereof.

32. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate having an indented section;
a gate dielectric layer formed disposed on the indented section;
a groove section formed disposed at a specified location in the semiconductor substrate;
a gate electrode formed disposed on the gate substrate and another portion of the gate electrode is above the semiconductor substrate,
wherein the gate electrode has a width that gradually increases from a bottom thereof up to toward an upper surface thereof, and a width of the upper surface of the gate electrode substantially equals the width of the groove.

33. (Cancelled)

34. (Currently Amended) A semiconductor device according to claim 1, wherein ~~at least another portion~~ a majority of the gate electrode is above the semiconductor substrate, and the first and second impurity diffusion layers.

35. (Previously Presented) A semiconductor device according to claim 1, wherein the third impurity diffusion layer is completely disposed between the first and second impurity diffusion layers.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

36. (Currently Amended) A semiconductor device according to claim + 7, wherein the extension regions ~~of the first and second impurity diffusion layers~~ are below the sidewall dielectric layer, and wherein an area below the gate dielectric layer is free of the extension regions.

37. (Cancelled).

38. (Currently amended) A semiconductor device according to claim 21, wherein ~~at least another portion a majority~~ of the gate electrode is above the semiconductor substrate, and the first and second impurity diffusion layers.

39. (Previously Presented) A semiconductor device according to claim 28, wherein the third impurity diffusion layer is completely disposed between the first and second impurity diffusion layers.

40. (Previously Presented) A semiconductor device according to claim 28, wherein the extension regions of the first and second impurity diffusion layers are below the sidewall dielectric layer, and wherein an area below the gate dielectric layer is free of the extension regions.

41. (Cancelled)

42. (Previously Presented) A semiconductor device according to claim 32, wherein a third impurity diffusion layer is completely disposed between the first and second impurity diffusion layers.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

43. (Previously Presented) A semiconductor device according to claim 32, further comprising:

extension regions in the first and second impurity diffusion layers, wherein the extension regions are below the sidewall dielectric layer, and wherein an area below the gate dielectric layer is free of the extension regions.

Please add the following new claims 44-63:

44. (New) A semiconductor device according to claim 1, wherein the gate electrode has a width that continuously increases from a bottom thereof up to an upper surface thereof.

45. (New) A semiconductor device according to claim 1, wherein the semiconductor substrate has a first surface and the indented section has a second surface below the first surface, and wherein the entire gate dielectric layer is disposed on the second surface.

46. (New) A semiconductor device according to claim 45, wherein the sidewall dielectric layer and the gate dielectric layer are disposed in contact with the indented section.

47. (New) A semiconductor device according to claim 45, wherein the sidewall dielectric layer has an outer surface that is substantially vertical with respect to the first surface of the semiconductor substrate.

48. (New) A semiconductor device according to claim 47, wherein the sidewall dielectric layer surrounds the gate dielectric layer.

49. (New) A semiconductor device according to claim 9, wherein at least a portion of the gate dielectric layer is above at least a portion of the sidewall dielectric layer, and wherein the sidewall dielectric layer is formed below the second metal silicide layer.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

50. (New) A semiconductor device according to claim 1, wherein a majority of the gate electrode is above the semiconductor substrate, the first impurity diffusion layer, and the second impurity diffusion layer.

51. (New) A semiconductor device according to claim 21, wherein the gate electrode has a width that continuously increases from a bottom thereof up to an upper surface thereof.

52. (New) A semiconductor device according to claim 21, wherein the semiconductor substrate has a first surface and the indented section has a second surface below the first surface, and wherein the entire gate dielectric layer is disposed on the second surface.

53. (New) A semiconductor device according to claim 52, wherein the sidewall dielectric layer and the gate dielectric layer are disposed in contact with the indented section.

54. (New) A semiconductor device according to claim 31, wherein the sidewall dielectric layer surrounds the gate dielectric layer.

55. (New) A semiconductor device according to claim 29, wherein at least a portion of the gate dielectric layer is above at least a portion of the sidewall dielectric layer, and wherein the sidewall dielectric layer is formed below the second metal silicide layer.

56. (New) A semiconductor device according to claim 32, wherein the gate electrode has a width that continuously increases from a bottom thereof up to an upper surface thereof.

57. (New) A semiconductor device according to claim 32, wherein the semiconductor substrate has a first surface and the indented section has a second surface below the first surface, and wherein the entire gate dielectric layer is disposed on the second surface.

Application No. 09/910,447
Amdt. Dated September 22, 2003
Reply to Office Action of June 23, 2003

Attorney Docket No. 81754.0064

58. (New) A semiconductor device according to claim 57, wherein the sidewall dielectric layer and the gate dielectric layer are disposed in contact with the indented section.

59. (New) A semiconductor device according to claim 57, wherein the sidewall dielectric layer has an outer surface that is substantially vertical with respect to the first surface of the semiconductor substrate .

60. (New) A semiconductor device according to claim 59, wherein the sidewall dielectric layer surrounds the gate dielectric layer and wherein at least a portion of the gate dielectric layer is above at least a portion of the sidewall dielectric layer.

61. (New) A semiconductor device according to claim 32, wherein a first metal silicide layer is disposed on the first and second impurity diffusion layers, and

wherein the gate electrode includes a second metal silicide layer on an upper surface thereof and the sidewall dielectric layer is formed below the second metal silicide layer.

62. (New) A semiconductor device according to claim 32, wherein surfaces of the first and second impurity diffusion layers are disposed at a position higher than a surface of an element isolation region.

63. (New) A semiconductor device according to claim 32, wherein a majority of the gate electrode is above the semiconductor substrate, and the first and second impurity diffusion layers.